

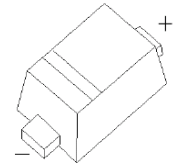


BAS516WT FAST SWITCHING DIODE



FEATURES

- Small Package
- Low Reverse Current
- Fast Switching Speed
- Surface Mount Package Ideally Suited for Automatic Insertion



MARKING:T4

SOD-523

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

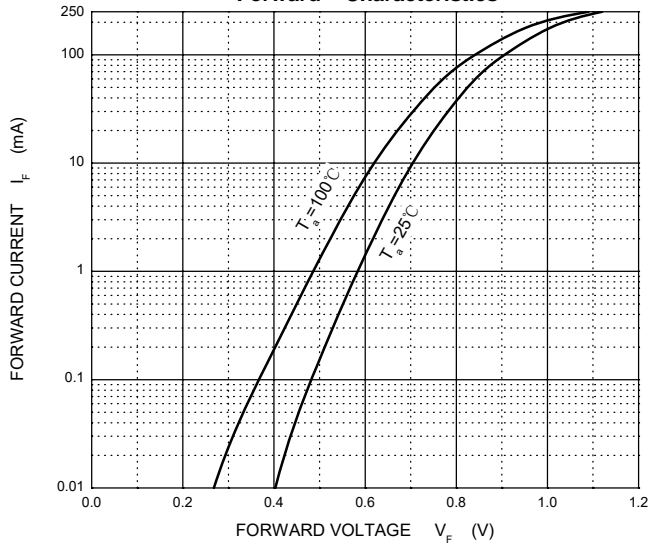
Symbol	Parameter	Value	Unit
V_{RM}	Non-Repetitive Peak Reverse Voltage	100	V
V_{RRM}	Peak Repetitive Reverse Voltage	75	V
V_{RWM}	Working Peak Reverse Voltage		
$V_{R(RMS)}$	RMS Reverse Voltage	53	V
I_o	Average Rectified Output Current	250	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	2.0	A
P_D	Power Dissipation	150	mW
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	833	$^{\circ}\text{C}/\text{W}$
T_J, T_{stg}	Operation Junction and Storage Temperature Range	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS($T_a=25^{\circ}\text{C}$ unless otherwise specified)

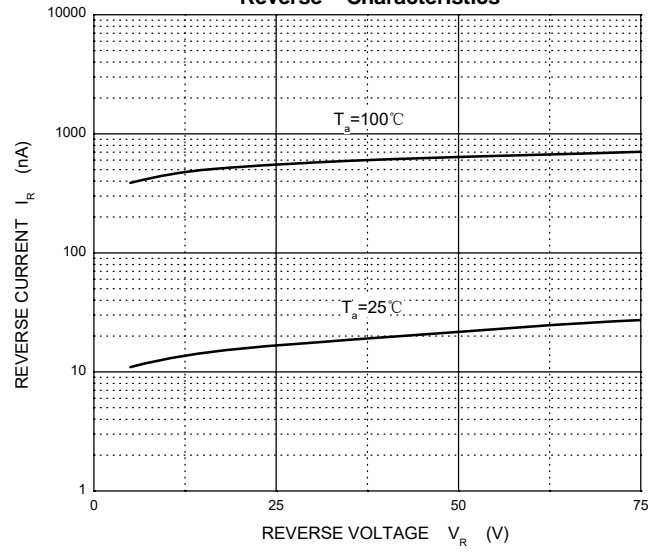
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=100\mu\text{A}$	75			V
Reverse current	I_R	$V_R=25\text{V}$			30	nA
		$V_R=75\text{V}$			1	μA
Forward voltage	V_F	$I_F=1\text{mA}$			0.715	V
		$I_F=10\text{mA}$			0.855	V
		$I_F=50\text{mA}$			1	V
		$I_F=150\text{mA}$			1.25	V
Total capacitance	C_{tot}	$V_R=0\text{V}, f=1\text{MHz}$			1	pF
Reverse recovery time	t_{rr}	$I_F=I_R=10\text{mA}, I_{rr}=0.1*I_R, R_L=100\Omega$			4	ns



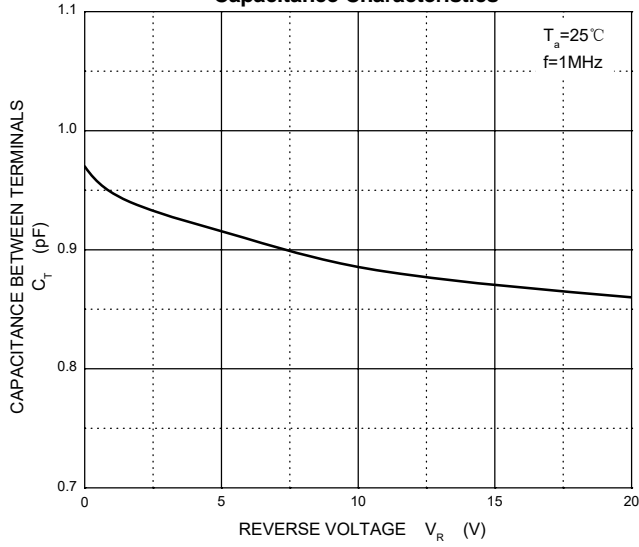
Forward Characteristics



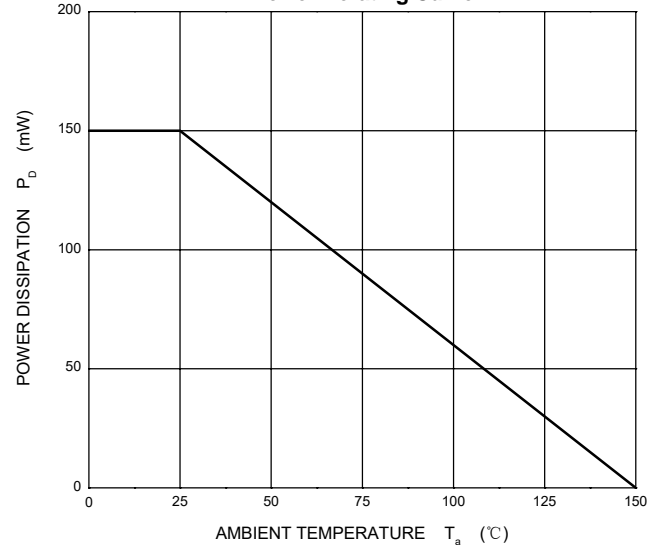
Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

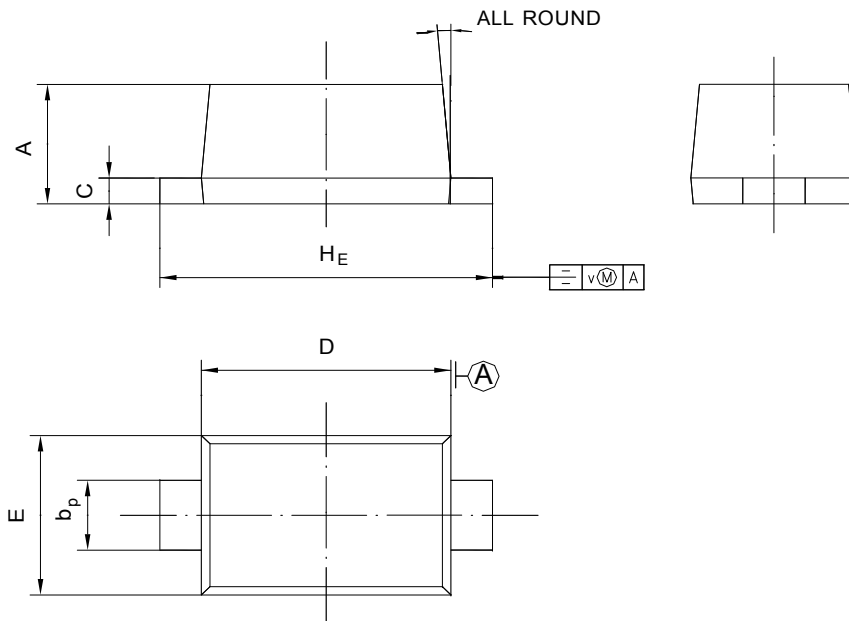




PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-523



UNIT	A	b _p	C	D	E	H _E	V	∠
mm	0.68 0.58	0.4 0.3	0.135 0.100	1.25 1.15	0.85 0.75	1.7 1.5	0.1	5°